

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) A semiconductor device comprising:
 - a semiconductor substrate;
 - a first insulating film formed above the semiconductor substrate and having a relative dielectric constant of 3.8 or less;
 - a conductor which covers a side face of the first insulating film at least near four corners of the semiconductor substrate, and at least an outer side face of which has a conductive barrier layer; and
 - a second insulating film covering the outer side face of the conductor and having a relative dielectric constant of over 3.8, at least a part of the second insulating film being formed at a same vertical position as the first insulating film.
2. (Previously Presented) A semiconductor device as set forth in claim 1, wherein the conductive barrier layer that the conductor contains one kind selected from a group consisting of titanium (Ti), tantalum (Ta), zirconium (Zr), and tungsten (W), and the conductor contains as a major component one kind selected from a group consisting of copper (Cu), aluminum (Al), and tin (Sn).
- 3.-6. (Canceled)

7. (Currently Amended) A semiconductor device as set forth in claim 1,
wherein the second insulating film ~~also covers~~ is extended so as to cover an
upper side of the first insulating film, the semiconductor device further comprising
a conductor pattern passing through the second insulating film positioned on the
upper side of the first insulating film.
8. (Canceled)
9. (Original) A semiconductor device as set forth in claim 7, further comprising a
conductive pattern buried in the first insulating film.
10. (Canceled)
11. (Original) A semiconductor device as set forth in claim 1, wherein the first
insulating film is constituted of a plurality of layers.
12. (Canceled)
13. (Original) A semiconductor device as set forth in claim 1, wherein the conductor
is formed in a ring shape covering an entire side face of the first insulating film.
14. (Canceled)

15. (Original) A semiconductor device as set forth in claim 1, wherein the second insulating film is at least one kind selected from a group consisting of silicon oxide (SiO_2), silicon nitride (SiN), silicon carbide (SiC), and silicon carbonitride (SiCN).

16.-20. (Canceled)